BCX17LT1, BCX18LT1, PNP BCX19LT1, NPN

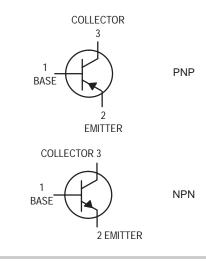
General Purpose Transistors

(Voltage and Current are negative for PNP transistors)



ON Semiconductor

Formerly a Division of Motorola http://onsemi.com





SOT-23 (TO-236AB) CASE 318 STYLE 6

DEVICE MARKING



See adjacent table for individual device marking information

x = Monthly Date Code

ORDERING INFORMATION

Device	Package	Shipping
BCX17LT1	SOT-23	3000 Units/Reel
BCX18LT1	SOT–23	3000 Units/Reel
BCX19LT1	SOT-23	3000 Units/Reel

MAXIMUM RATINGS

		Val		
Rating	Symbol	BCX17LT1 BCX19LT1	BCX18LT1	Unit
Collector–Emitter Voltage	VCEO	45	25	Vdc
Collector-Base Voltage	VCBO	50	30	Vdc
Emitter–Base Voltage	VEBO	5.0		Vdc
Collector Current — Continuous	IC	500		mAdc

DEVICE MARKING

BCX17LT1 = T1; BCX18LT1 = T2; BCX19LT1 = U1

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (1) $T_A = 25^{\circ}C$	PD	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	R _{θJA}	556	°C/W
Total Device Dissipation Alumina Substrate, $^{(2)} T_A = 25^{\circ}C$	PD	300	mW
Derate above 25° C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	R _{θJA}	417	°C/W
Junction and Storage Temperature	TJ, T _{stg}	-55 to +150	°C

1. FR–5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina

BCX17LT1, BCX18LT1, PNP BCX19LT1, NPN

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

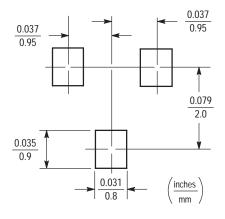
Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•			•	
Collector–Emitter Breakdown Voltage ($I_C = 10 \text{ mAdc}, I_B = 0$)	BCX17, 19 BCX18	V(BR)CEO	45 25			Vdc
Collector–Emitter Breakdown Voltage $(I_C = 10 \ \mu Adc, I_C = 0)$	BCX17, 19 BCX18	V(BR)CES	50 30			Vdc
Collector Cutoff Current (V _{CB} = 20 Vdc, I _E = 0) (V _{CB} = 20 Vdc, I _E = 0, T _A = 150°C)		Ісво			100 5.0	nAdc μAdc
Emitter Cutoff Current ($V_{EB} = 5.0 \text{ Vdc}, I_C = 0$)		IEBO	_	_	10	μAdc
ON CHARACTERISTICS		•			•	
DC Current Gain $(I_{C} = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$ $(I_{C} = 300 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$ $(I_{C} = 500 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$		hFE	100 70 40	 	600 — —	_
Collector–Emitter Saturation Voltage (I _C = 500 mAdc, I _B = 50 mAdc)		V _{CE(sat)}	—	—	0.62	Vdc
Base–Emitter On Voltage (I _C = 500 mAdc, V _{CE} = 1.0 Vdc)		V _{BE(on)}	—	—	1.2	Vdc

INFORMATION FOR USING THE SOT-23 SURFACE MOUNT PACKAGE

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.





SOT-23 POWER DISSIPATION

The power dissipation of the SOT–23 is a function of the pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by $T_{J(max)}$, the maximum rated junction temperature of the die, $R_{\theta JA}$, the thermal resistance from the device junction to ambient, and the operating temperature, T_A . Using the values provided on the data sheet for the SOT–23 package, P_D can be calculated as follows:

$$P_{D} = \frac{T_{J(max)} - T_{A}}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature T_A of 25°C, one can calculate the power dissipation of the device which in this case is 225 milliwatts.

$$P_{D} = \frac{150^{\circ}C - 25^{\circ}C}{556^{\circ}C/W} = 225 \text{ milliwatts}$$

The 556°C/W for the SOT–23 package assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 225 milliwatts. There are other alternatives to achieving higher power dissipation from the SOT–23 package. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad[™]. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

SOLDERING PRECAUTIONS

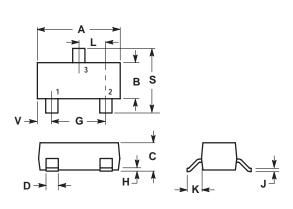
The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference shall be a maximum of 10°C.
- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient shall be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.

* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

PACKAGE DIMENSIONS

SOT-23 (TO-236AB) CASE 318-08 **ISSUE AF**



NOTES: DIMENSIONING AND TOLERANCING PER ANSI

1

Y14.5M, 1982. CONTROLLING DIMENSION: INCH. 2

MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.1102	0.1197	2.80	3.04	
В	0.0472	0.0551	1.20	1.40	
С	0.0350	0.0440	0.89	1.11	
D	0.0150	0.0200	0.37	0.50	
G	0.0701	0.0807	1.78	2.04	
Н	0.0005	0.0040	0.013	0.100	
J	0.0034	0.0070	0.085	0.177	
К	0.0140	0.0285	0.35	0.69	
L	0.0350	0.0401	0.89	1.02	
S	0.0830	0.1039	2.10	2.64	
V	0.0177	0.0236	0.45	0.60	

STYLE 6: PIN 1. BASE 2. EMITTER

> COLLECTOR 3

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